

Turbo 2 ultrafast high voltage rectifier

Technical Literature

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STTH200L06TV

Turbo 2 ultrafast high voltage rectifier

Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses

Description

The STTH200L06TV, which is using ST Turbo 2 600 V technology, is specially suited for use in switching power supplies, and industrial applications (such as welding), as rectification diode.

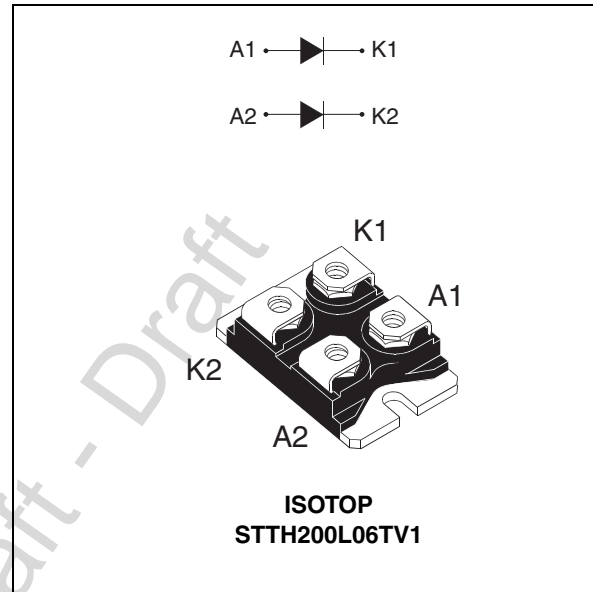


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	Up to 2 x 120 A
V_{RRM}	600 V
T_j	150 °C
V_F (typ)	0.95 V
t_{rr} (max)	80 ns

TM: ISOTOP is a trademark of STMicroelectronics

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter		Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		600	V	
$I_{F(RMS)}$	Forward rms current		180	A	
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 65\text{ }^\circ\text{C}$	Per diode	100	A
		$T_c = 35\text{ }^\circ\text{C}$	Per diode	120	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ Sinusoidal	800	A	
T_{stg}	Storage temperature range		-55 to + 150	$^\circ\text{C}$	
T_j	Maximum operating junction temperature		150	$^\circ\text{C}$	

Table 3. Thermal parameter

Symbol	Parameter		Maximum	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.60	$^\circ\text{C/W}$
		Total	0.35	
$R_{th(c)}$	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P (\text{diode1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode2}) \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ }^\circ\text{C}$	$V_R = V_{RRM}$			100	μA
		$T_j = 125\text{ }^\circ\text{C}$			100	1000	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 100\text{ A}$			1.55	V
		$T_j = 150\text{ }^\circ\text{C}$			0.95	1.20	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$
2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 0.93 \times I_{F(AV)} + 0.0027 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 0.5\text{ A}$, $I_{rr} = 0.25\text{ A}$, $I_R = 1\text{ A}$			80	ns
			$I_F = 1\text{ A}$, $di_F/dt = 50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$		85	120	
I_{RM}	Reverse recovery current	$T_j = 125\text{ }^\circ\text{C}$	$I_F = 100\text{ A}$, $di_F/dt = 400\text{ A}/\mu\text{s}$, $di_F/dt = 100\text{ A}/\mu\text{s}$		15	20	A
t_{fr}	Forward recovery time	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 100\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			700	ns
V_{FP}	Forward recovery voltage	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 100\text{ A}$, $di_F/dt = 200\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$		3.4		V

Figure 1. Conduction losses versus average forward current (per diode)

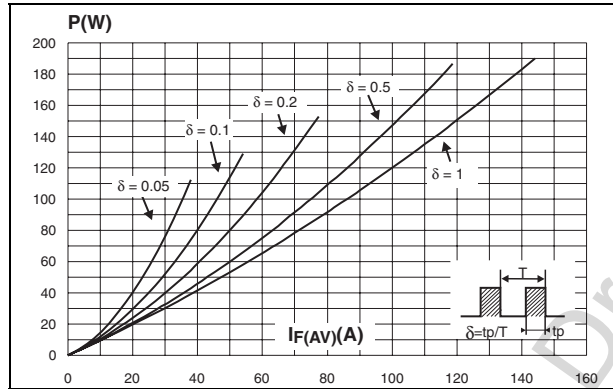


Figure 2. Forward voltage drop versus forward current (per diode)

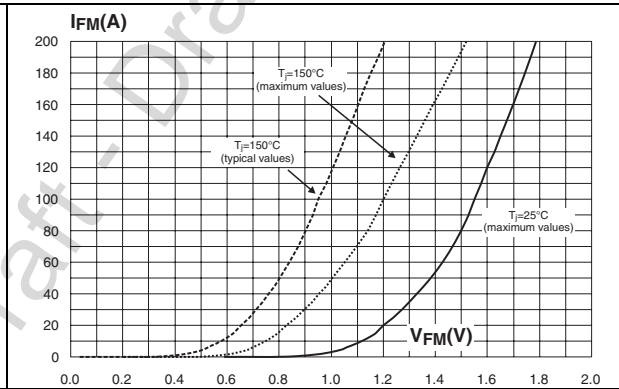


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

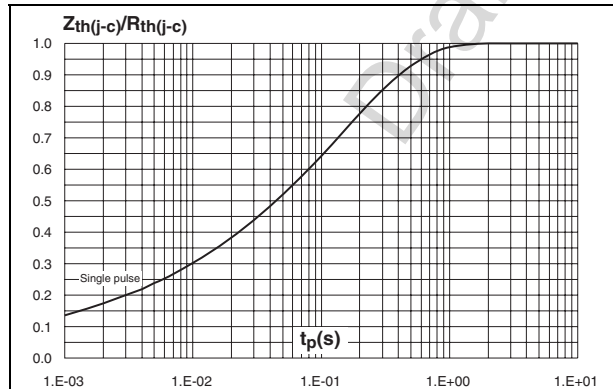


Figure 4. Peak reverse recovery current versus di/dt (typical values, per diode)

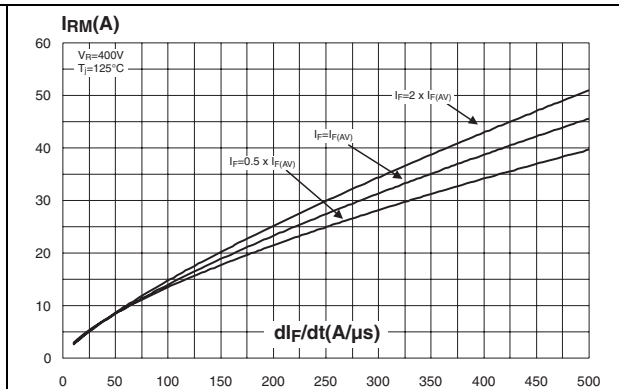


Figure 5. Reverse recovery time versus di_F/dt (typical values, per diode)

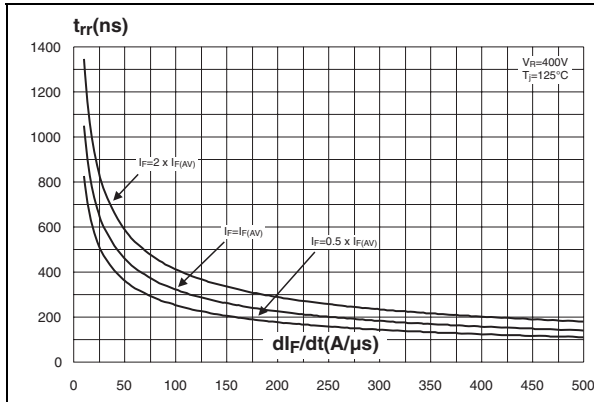


Figure 6. Reverse recovery charges versus di_F/dt (typical values, per diode)

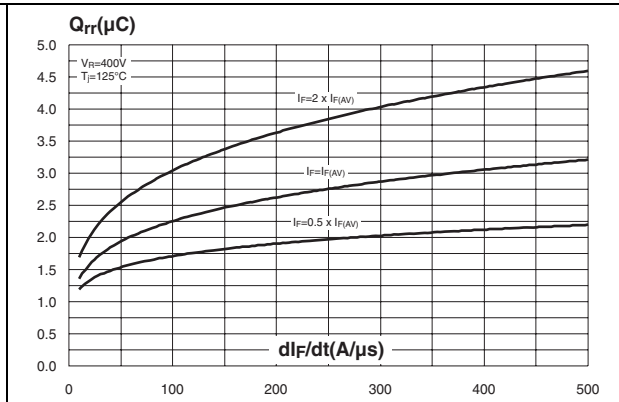


Figure 7. Reverse recovery softness factor versus di_F/dt (typical values, per diode)

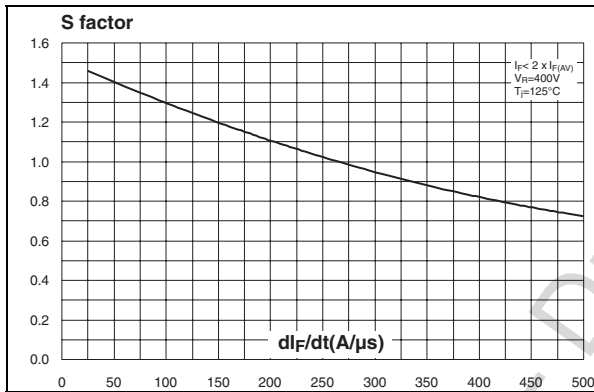


Figure 8. Relative variations of dynamic parameters versus junction temperature

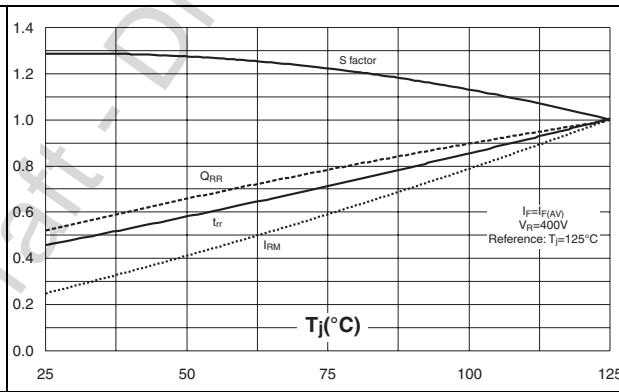


Figure 9. Transient peak forward voltage versus di_F/dt (typical values, per diode)

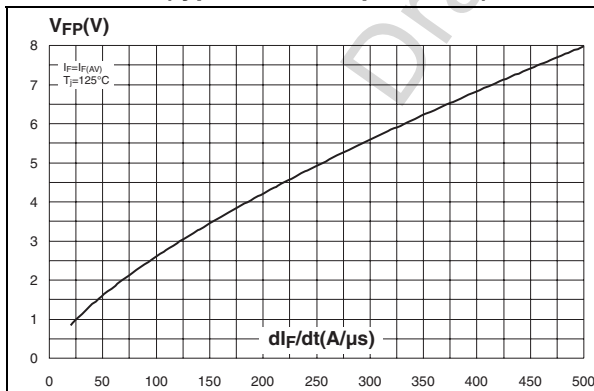


Figure 10. Forward recovery time versus di_F/dt (typical values, per diode)

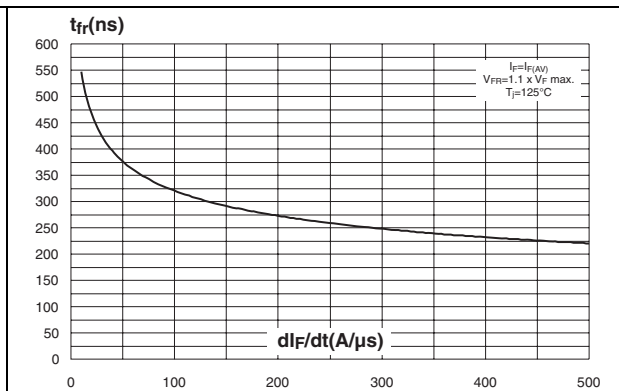
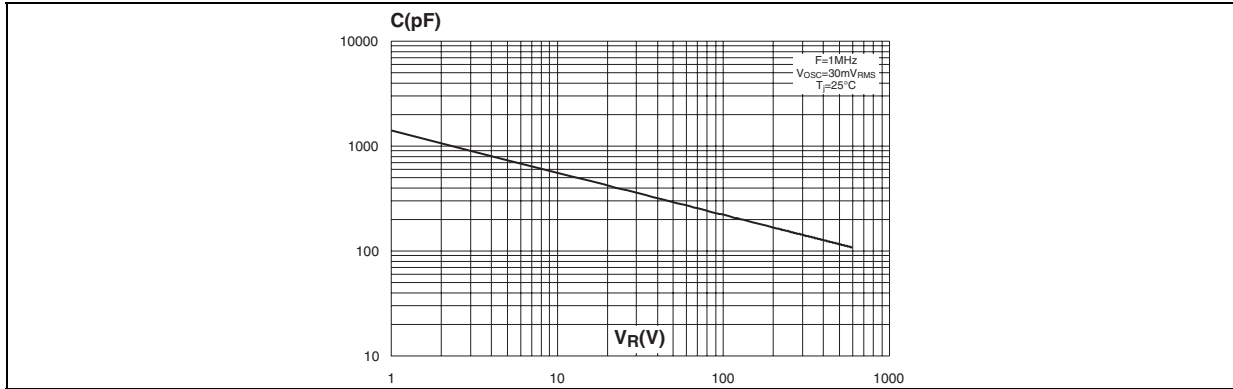


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



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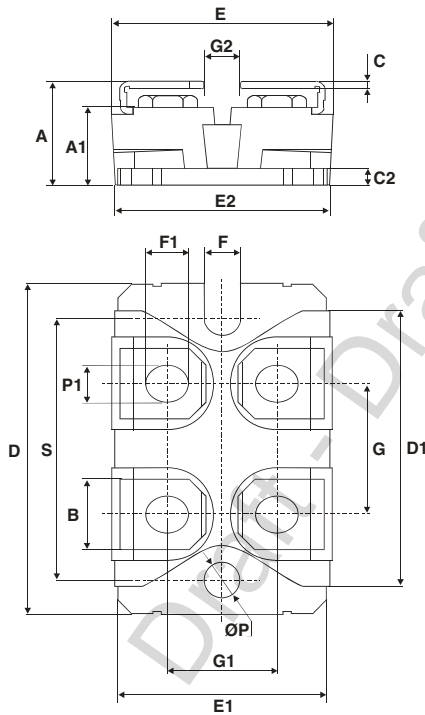
2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. ISOTOP dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH200L06TV1	STTH200L06TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
07-Sep-2004	1	First issue.
05-Sep-2011	2	Updated Figure 6 .

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